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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

JAMAL RAMDANI ET AL

SERIAL NO: 09/766,046

FILED: JANUARY 19, 2001

FOR: STRUCTURE AND METHOD FOR:
FABRICATING GaN DEVICES
UTILIZING THE FORMATION OF
A COMPLIANT SUBSTRATE

: EXAMINER: MUNSON, G. M.

: GROUP ART UNIT: 2811

TECHNOLOGY CENTER 2800

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F Jones
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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated April 30, 2002, Applicants respectfully request reconsideration in view of the following amendment and remarks.

IN THE CLAIMS

Please amend Claim 1 as follows:

- a
1. (Amended) A semiconductor structure comprising:
a monocrystalline substrate;
an amorphous layer formed on the substrate; and
a first monocrystalline nitride material layer overlying the amorphous layer and
formed of at least one selected from the group consisting of GaN, GaInN, AlGaIn, SiN and
AlN, wherein the first monocrystalline nitride material layer is formed by nitridation of a first